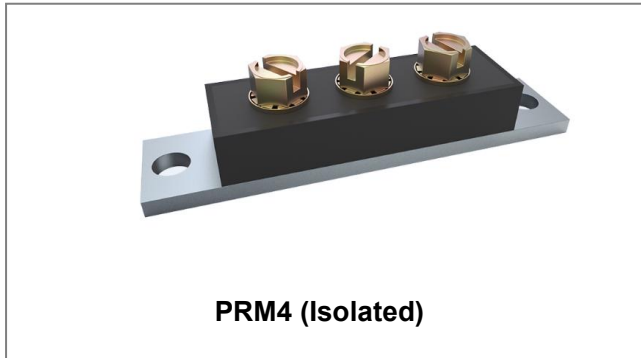


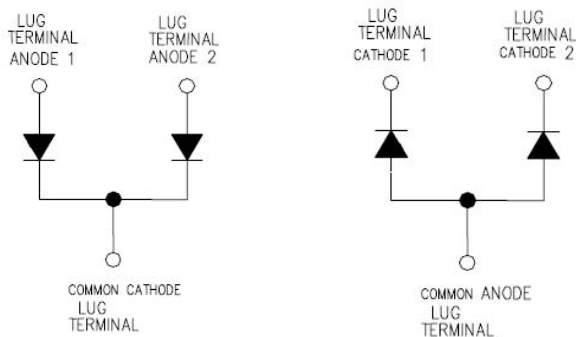
203CMQ080/203CMQ100 SCHOTTKY RECTIFIER



Features

- 175°C T_J operation
- Center tap module
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



203CMQ100

203CMQ100R

Applications

- High current switching power supply
- Plating power supply
- Free-Wheeling diodes
- Reverse battery protection
- Converters
- UPS System
- Welding

Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
			80	203CMQ080/R	
Peak Repetitive Reverse Voltage	V _{RRM}	-	80	203CMQ080/R	V
Working Peak Reverse Voltage DC Blocking Voltage	V _{RWM} V _R		100	203CMQ100/R	
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @T _C =110°C, rectangular wave form	100(Per Leg) 200(Per Device)		A
Peak One Cycle Non-Repetitive Surge Current (Per Leg)	I _{FSM}	8.3 ms, half Sine pulse	2520		A
Non-Repetitive Avalanche Energy(Peg Leg)	E _{AS}	T _J =25°C, I _{AS} =1A, L=30mH	15		mJ
Repetitive Avalanche Current (Peg Leg)	I _{AR}	Current decaying linearly to zero in 1 μsec Frequency limited by T _J max. V _A =1.5×V _R typical	1		A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop(Per Leg)*	V _{F1}	@ 100A, Pulse, T _J = 25 °C @ 200A, Pulse, T _J = 25 °C	0.79 -	0.86 1.03	V
	V _{F2}	@ 100A, Pulse, T _J = 125 °C @ 200A, Pulse, T _J = 125 °C	0.61 -	0.70 0.84	V
Reverse Current(Per Leg)*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.001	3	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	0.8	40	mA
Junction Capacitance(Per leg)	C _T	@V _R = 5V, T _C = 25 °C f _{sig} = 1MHz	2400	2650	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

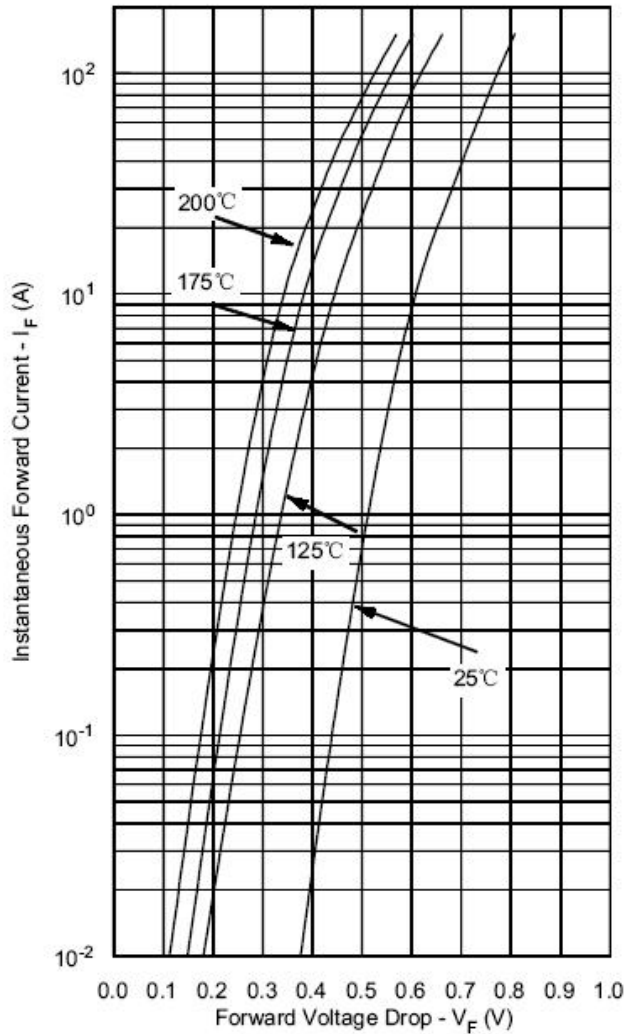
* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

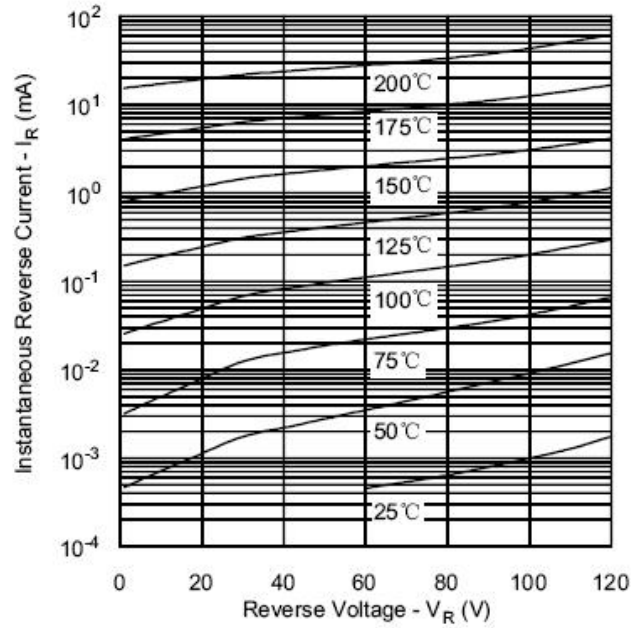
Characteristics	Symbol	Condition	Specification	Units	
Junction Temperature	T _J	-	-55 to +175	°C	
Storage Temperature	T _{stg}	-	-55 to +175	°C	
Typical Thermal Resistance Junction to Case(Per leg)	R _{θJC}	DC operation	0.70	°C/W	
Typical Thermal Resistance Junction to Case(Per package)	R _{θJC}	DC operation	0.35	°C/W	
Typical Thermal Resistance, case to Heat Sink	R _{θcs}	Mounting surface, smooth and greased	0.10	°C/W	
Mounting Torque	T _M	-	Mounting Torque	24(min) 35(max)	Kg-cm
			Terminal Torque	35(min) 46(max)	
Approximate Weight	wt	-	79	g	
Case Style	PRM4 Isolated				

Ratings and Characteristics Curves

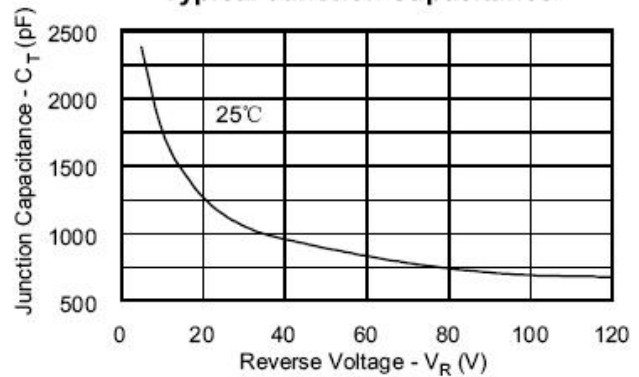
Typical Forward Characteristics



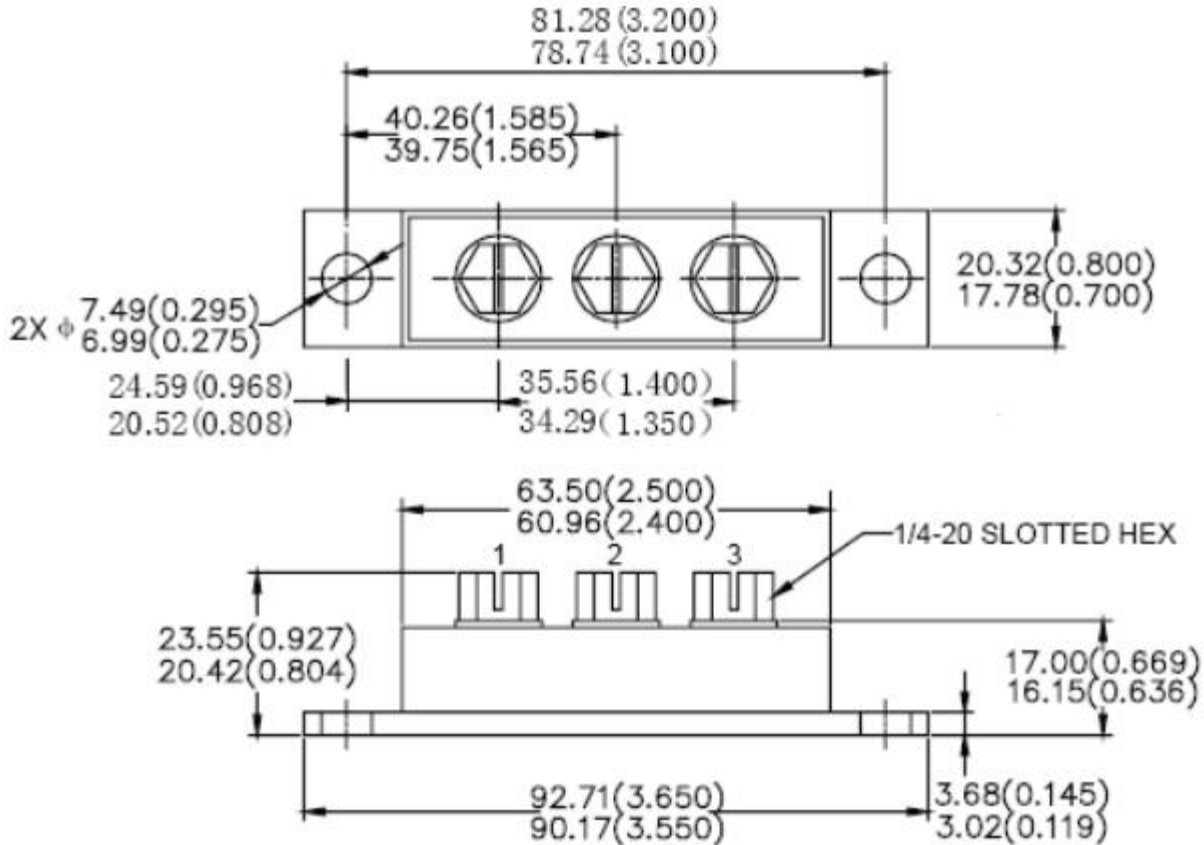
Typical Reverse Characteristics



Typical Junction Capacitance

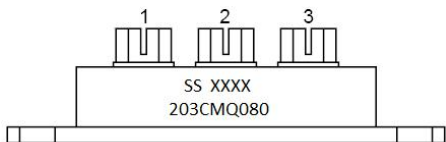


Mechanical Dimensions PRM4 Isolated (Millimeters/Inches)



Please Note: Anode 1 = Terminal 1; Anode 2 = Terminal 3; Common Cathode = Terminal 2
Suffix R Denotes for Reversed Polarity.

Marking Diagram



Where XXXX is YYWW

203CMQ080 = Part name
SS = SS
YY = Year
WW = Week

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
203CMQ SERIES	PRM4 Isolated (Pb-Free)	9 pcs/box

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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